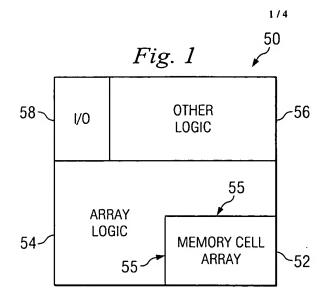
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. . . .

TO BIT LINE(S)
OR WORD LINE(S)
60

MTJ
CONFIGURATION

SWITCHING
DEVICE
68

TO WORD LINE
OR BIT LINE

Fig. 3

TO BIT LINE
OR WORD LINE

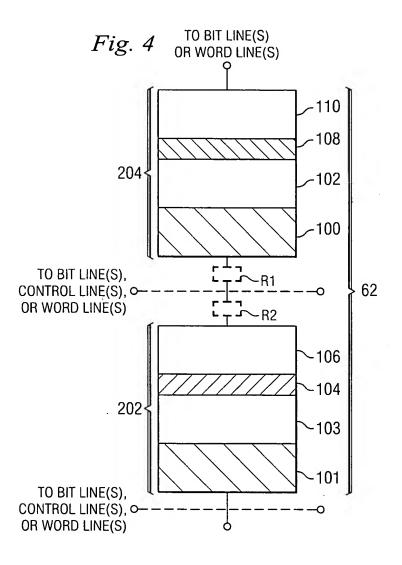
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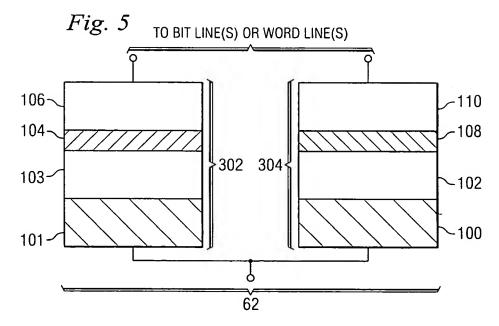
-106

-104

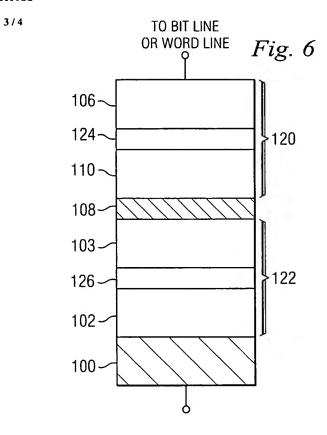
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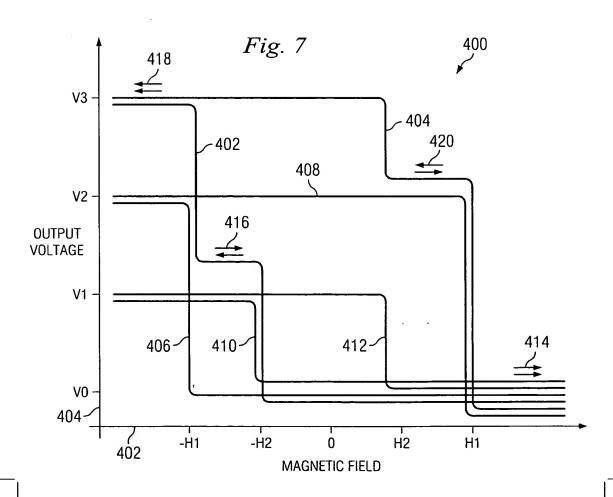
2/4





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Lin et al.
MULTI-SENSING LEVEL MRAM STRUCTURE
WITH DIFFERENT MAGNETORESISTANCE
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